# UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 7,023,739 B2

Page 1 of 1

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INVENTOR(S)

: April 4, 2006 : En-Hsing Chen et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

### Column 22:

Line 43, the words "programmed stated" should read -- programmed state --.

## Column 23:

Line 4, the word "suicide" should read -- silicide --.

# Column 27:

Line 1, the words "A 2556 kb 3.0V ITIMTJ" should read -- A 256 kb 3.0V 1M1MTJ --.

## Column 28:

Line 47, the word "use" should read -- used --.

### Column 36:

Line 18, the word "NAND)" should read -- NAND --.

Signed and Sealed this

Eighth Day of August, 2006

JON W. DUDAS Director of the United States Patent and Trademark Office